

# INTERNATIONAL STANDARD

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**Semiconductor devices - Mechanical and climatic test methods -  
Part 22-2: Bond strength - Wire bond shear test methods**



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## CONTENTS

FOREWORD .....	4
1 Scope .....	6
2 Normative references .....	6
3 Terms and definitions .....	6
3.1 Terms and definitions .....	7
3.2 Terms and definitions applicable to Annex B .....	8
4 Apparatus and material required .....	8
4.1 Inspection equipment .....	8
4.2 Measurement equipment .....	8
4.3 Workholder .....	9
4.4 Bond shear equipment .....	9
4.5 Bond shear chisel tool setup .....	9
5 Procedure .....	9
5.1 Calibration .....	9
5.2 Visual examination of bonds to be tested after decapsulation .....	10
5.2.1 Usage of visual examination .....	10
5.2.2 Bond pad examination and acceptability criteria for both Al and Cu bond pad metallization .....	10
5.2.3 Copper bond and Cu wire examination and acceptability criteria .....	10
5.3 Measurement of the ball bond diameter to determine the ball bond shear failure criteria .....	10
5.4 Performing the bond shear test .....	11
5.5 Examination of sheared bonds .....	12
5.6 Bond shear codes for ball bonds .....	12
5.6.1 General .....	12
5.6.2 Type 1 – Bond lift .....	16
5.6.3 Type 2 – Bond shear .....	17
5.6.4 Type 3 – Cratering .....	19
5.6.5 Type 4 – arm contacts specimen (bonding surface contact) .....	21
5.6.6 Type 5 – shearing skip .....	21
5.6.7 Type 6 – Bond pad (or bonding surface) lift .....	21
5.7 Bond shear data .....	22
6 Summary .....	22
Annex A (informative) Performing this test method on "stitch on ball" bonds .....	23
Annex B (informative) Performing this test method on ultrasonic wedge bonds .....	25
B.1 General .....	25
B.2 Additions and modifications of the main text .....	25
B.2.1 Addition to Clause 1 .....	25
B.2.2 Addition to Clause 3 .....	25
B.2.3 Replacement of 4.4 .....	25
B.2.4 Replacement of 5.4 .....	26
B.2.5 Replacement of 5.5 .....	26
B.2.6 Additional text to 5.6 .....	26
B.2.7 Replacement of Clause 6 .....	26
Annex C (informative) Performing shear testing when a tool cannot reach below bond centreline .....	27

Annex D (informative) Concerns with decapsulation processes for devices with copper wirebonds.....	29
Annex E (informative) Bond contact area – Valid method for comparing shear force .....	32
Bibliography.....	34
Figure 1 – Bond shear set-up for bond on die bonding pad .....	7
Figure 2 – Proper height placement of shear tool with respect to ball centre line .....	9
Figure 3 – Ball bond measurement: side view and top view (for symmetrical versus asymmetrical) .....	11
Figure 4 – Type 1: Bond lift – Gold/aluminium .....	12
Figure 5 – Type 1: Bond lift – Copper/aluminium, copper/copper and gold/gold.....	12
Figure 6 – Type 1: Bond lift – All metal systems on leadframe or substrate.....	13
Figure 7 – Type 2: Bond shear – All metal systems – Variation A – Separation within bonding surface metalization .....	13
Figure 8 – Type 2: Bond shear – Gold/aluminium – Variation B – Separation wholly within intermetallic layer.....	13
Figure 9 – Type 2: Bond shear – All metal systems and surfaces, except Gold/aluminium – Variation B – Separation at bonding surface.....	14
Figure 10 – Type 2: Bond shear – All metal systems and bonding surfaces – Variation C – Separation at material interface and within bulk material.....	14
Figure 11 – Type 2: Bond shear – All metal systems – Variation D – Separation within ball bond .....	14
Figure 12 – Type 2: Bond shear – All metal systems on leadframe or substrate – Variation D – Separation within ball bond.....	15
Figure 13 – Type 3: Cratering .....	15
Figure 14 – Type 4: Bonding surface contact.....	15
Figure 15 – Type 5: Shearing skip.....	16
Figure 16 – Type 6: Bonding pad surface lift .....	16
Figure 17 – Type 6: Leadframe or substrate bond pad or bonding surface metalization lift.....	16
Figure 18 – Imprints on Al pad from lifted bonds with no evidence of shearing (Type 1) .....	17
Figure 19 – Shear of aluminium pad (with copper wire) (Type 2 – Variation A) .....	18
Figure 20 – Shear wholly within gold/aluminium intermetallic layer (Type 2 – Variation B) .....	18
Figure 21 – Shear in bulk copper ball bond and at material interface (Type 2 – Variation C) .....	19
Figure 22 – Shear wholly within gold ball bond (Type 2 – Variation D).....	19
Figure 23 – Shear wholly within Cu ball bond (Type 2 – Variation D).....	19
Figure 24 – Bond pad cratering after shear test .....	20
Figure 25 – Bond pad cratering (pad and ball view) and validation of crack and thin Al on another pad.....	20
Figure 26 – Images of shear tool contacting the bonding surface (shear tool set too low) .....	21
Figure 27 – Images of shearing skip (shear tool set too high).....	21
Figure 28 – Images of bonding surface lifting .....	22
Figure A.1 – Top view of "stitch on ball" bond.....	23
Figure A.2 – Side view of "stitch on ball" bond.....	23

Figure A.3 – Die to die bonding.....	24
Figure A.4 – "Reverse" bond, with ball on leadframe .....	24
Figure C.1 – Passivation preventing proper height placement of shear tool.....	27
Figure C.2 – Remnant due to shear tool placement above centreline .....	27
Figure C.3 – Views of excessive Al splash .....	28
Figure D.1 – Images of copper ball bonds showing severe damage from etching process .....	29
Figure D.2 – Comparison images showing degree of Cu attack due to two different etchants .....	29
Figure D.3 – Stitch bond after decapsulation using laser ablation .....	30
Figure D.4 – Die and wirebonds decapsulated using laser ablation .....	31
Figure E.1 – Sample cross section of a copper wire bond .....	32
Figure E.2 – Image analysis of pixel distribution within the fitted circle (represents ball) .....	33
Figure E.3 – Images of "optical versus SEM" correlation study .....	33

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### **Semiconductor devices - Mechanical and climatic test methods - Part 22-2: Bond strength - Wire bond shear test methods**

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This International Standard is to be used in conjunction with IEC 60749-22-1:2025.

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This edition includes the following significant technical changes with respect to the previous edition:

- a) Major update, including new techniques and use of new materials (e.g. copper wire) involving a complete rewrite as two separate subparts (this document and IEC 60749-22-1).

The text of this International Standard is based on the following documents:

Draft	Report on voting
47/2959/FDIS	47/2981/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at [www.iec.ch/members\\_experts/refdocs](http://www.iec.ch/members_experts/refdocs). The main document types developed by IEC are described in greater detail at [www.iec.ch/publications](http://www.iec.ch/publications).

A list of all parts in the IEC 60749 series, published under the general title *Semiconductor devices - Mechanical and climatic test methods*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under [webstore.iec.ch](http://webstore.iec.ch) in the data related to the specific document. At this date, the document will be

- reconfirmed,
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- revised.

## 1 Scope

This part of IEC 60749 establishes a means for determining the strength of a ball bond to a die or package bonding surface and can be performed on pre-encapsulation or post-encapsulation devices. This measure of bond strength is extremely important in determining two features:

- a) the integrity of the metallurgical bond which has been formed, and
- b) the quality of ball bonds to die or package bonding surfaces.

This test method covers thermosonic (ball) bonds made with small diameter wire from 15  $\mu\text{m}$  to 76  $\mu\text{m}$  (0,000 6" to 0,003").

This test method can only be used when the bonds are large enough to allow for proper contact with the shear test chisel and when there are no adjacent interfering structures that would hinder the movement of the chisel. For consistent shear results the ball height will be at least 4,0  $\mu\text{m}$  (0,000 6 ") for ball bonds, which is the current state of the art for bond shear test equipment at the time of this revision.

This test method can also be used on ball bonds that have had their wire removed and on to which a second bond wire (typically a stitch bond) is placed. This is known as "stitch on ball" and "reverse bonding". See Annex A for additional information.

The wire bond shear test is destructive. It is appropriate for use in process development, process control, or quality assurance, or both.

This test method can be used on ultrasonic (wedge) bonds, however its use has not been shown to be a consistent indicator of bond integrity. See Annex B for information on performing shear testing on wedge bonds.

This test method does not include bond strength testing using wire bond pull testing. Wire bond pull testing is described in IEC 60749-22-1.

## 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60749-22-1, *Semiconductor devices - Mechanical and climatic test methods - Part 22-1: Bond strength testing - Wire bond pull test methods*